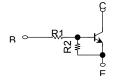
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

# RN1967FS,RN1968FS,RN1969FS

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

- Two devices are incorporated into a fine pitch Small Mold (6 pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Complementary to RN2967FS~RN2969FS

#### **Equivalent Circuit and Bias Resistor Values**



Type No.	R1 (kΩ)	R2 (kΩ)
RN1967FS	10	47
RN1968FS	22	47
RN1969FS	47	22

0.02 1.0±0.05 0.7±0.05 0.7±0.05 0.7±0.05 0.7±0.05 0.7±0.05 0.7±0.05 0.7±0.05 0.7±0.05 0.04 0.05 0.04 0.05 0.05 0.05 0.05		0.1±0.05 + 0.15±0.05 0.0	
0.48 -0.04	↓ ┌		
fS6	1.EMIITTER1 2.EMITTER2 3.BASE2 4.COLLECTOR2 5.BASE1 6.COLLECTOR1	(E1) (E2) (B2) (C2) (B1) (C1)	
JEDEC	> _		
JEITA	_		
TOSHI	TOSHIBA 2-1F1C		

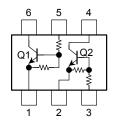
Weight:0.001g (typ.)

#### Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage	RN1967FS~	V <sub>CBO</sub>	20	V	
Collector-emitter voltage	1969FS	V <sub>CEO</sub>	20	V	
	RN1967FS		6	V	
Emitter-base voltage	RN1968FS	V <sub>EBO</sub>	7		
	RN1969FS		15		
Collector current		Ι <sub>C</sub>	50	mA	
Collector power dissipation	RN1967FS~	N1967FS~ P <sub>C</sub> (Note)		mW	
Junction temperature	RN1969FS	Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

Note: Total rating

## Equivalent Circuit (top view)



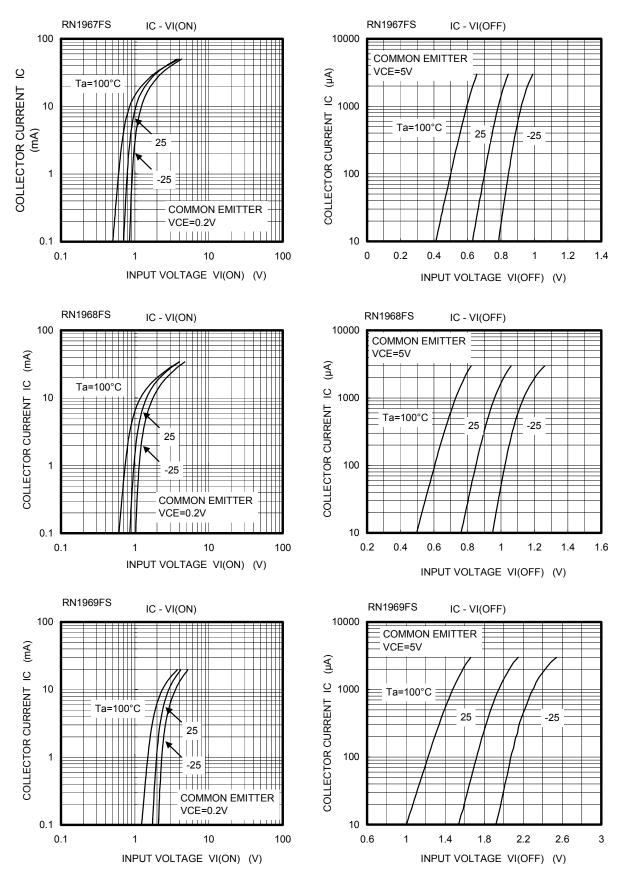
Unit: mm

#### Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN1967FS~1969FS	I <sub>CBO</sub>	$V_{CB} = 20 \text{ V}, \text{ I}_{E} = 0$	_		100	nA
		I <sub>CEO</sub>	$V_{CE} = 20 \text{ V}, \text{ I}_{B} = 0$	_		500	
	RN1967FS	IEBO	$V_{EB}=6V,\ I_C=0$	0.088	_	0.131	mA
Emitter cut-off current	RN1968FS		$V_{EB}=7V,\ I_C=0$	0.085	_	0.126	
	RN1969FS		$V_{EB}=15V,\ I_C=0$	0.182		0.271	
	RN1967FS	h <sub>FE</sub>	$V_{CE} = 5 V, I_{C} = 10 mA$	120		_	
DC current gain	RN1968FS			120	_	_	
	RN1969FS			100			
Collector-emitter saturation voltage	RN1967FS~1969FS	V <sub>CE (sat)</sub>	$\begin{array}{l} I_C = 5 \text{ mA}, \\ I_B = 0.25 \text{ mA} \end{array}$	_	_	0.15	V
	RN1967FS	V <sub>I (ON)</sub>	$V_{CE} = 0.2 \text{ V}, I_{C} = 5 \text{ mA}$	0.7		1.5	v
Input voltage (ON)	RN1968FS			0.8		2.2	
	RN1969FS			1.6		5.0	
	RN1967FS	VI (OFF)	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 0.1 \text{ mA}$	0.5		1.0	V
Input voltage (OFF)	RN1968FS			0.6	_	1.1	
	RN1969FS			1.3		2.6	
Collector output capacitance	RN1967FS~1969FS	C <sub>ob</sub>	$\begin{array}{l} V_{CB}=10 \ V, \ I_{E}=0, \\ f=1 \ MHz \end{array}$	_	1.2	_	pF
	RN1967FS	R1	_	8	10	12	kΩ
Input resistor	RN1968FS			17.6	22	26.4	
	RN1969FS			37.6	47	56.4	
	RN1967FS	R1/R2	R2	0.17	0.213	0.255	
Resistor ratio	RN1968FS			0.374	0.468	0.562	
	RN1969FS			1.71	2.14	2.56	

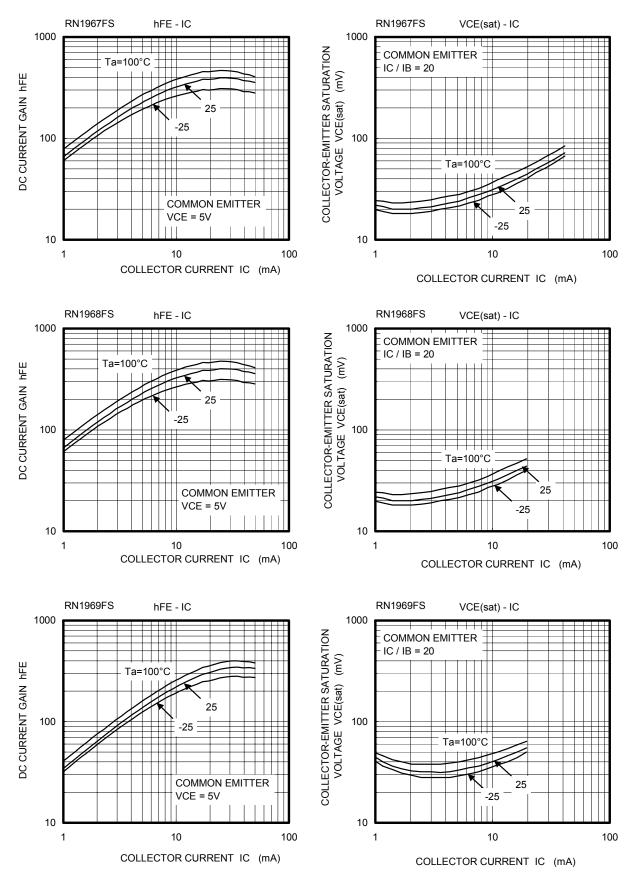
## <u>TOSHIBA</u>

#### (Q1,Q2 common)



### <u>TOSHIBA</u>

#### (Q1,Q2 common)



Type Name	Marking	
RN1967FS	6 5 4 Type name J6 J6 1 2 3	
RN1968FS	6 5 4 Type name J7 J7 1 2 3	
RN1969FS	6 5 4 Type name J8 J8 1 2 3	

#### HANDLING PRECAUTION

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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